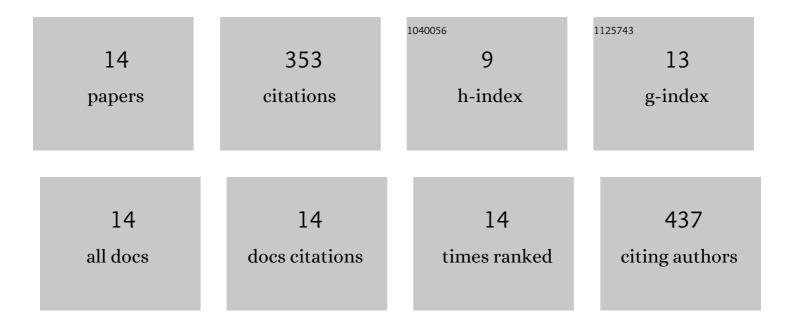
Nupur Bhargava

List of Publications by Year in descending order

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Νιίσιο Βηλοςλυλ

#	Article	IF	CITATIONS
1	Abrupt SiGe-to-Si interface: influence of chemical vapor deposition processes and characterization by different metrology techniques. Semiconductor Science and Technology, 2018, 33, 104003.	2.0	2
2	Thermal Stability of Annealed Germanium-Tin Alloys Grown by Molecular Beam Epitaxy. Journal of Electronic Materials, 2017, 46, 1620-1627.	2.2	5
3	Fundamentals of Ge 1â^'x Sn x and Si y Ge 1â^'x-y Sn x RPCVD epitaxy. Materials Science in Semiconductor Processing, 2017, 70, 38-43.	4.0	36
4	As doping of Si–Ge–Sn epitaxial semiconductor materials on a commercial CVD reactor. Semiconductor Science and Technology, 2017, 32, 094003.	2.0	6
5	Strain engineering in epitaxial Ge _{1â^'} <i>_x</i> Sn _{<i>x</i>/i>S} : a path towards low-defect and high Sn-content layers. Semiconductor Science and Technology, 2017, 32, 124006.	2.0	35
6	Theoretical study of the effects of strain balancing on the bandgap of dilute nitride InGaSbN/InAs superlattices on GaSb substrates. Infrared Physics and Technology, 2015, 69, 211-217.	2.9	1
7	Infrared photoresponse of GeSn/n-Ge heterojunctions grown by molecular beam epitaxy. Optics Express, 2014, 22, 11029.	3.4	23
8	Structural Properties of Boron-Doped Germanium-Tin Alloys Grown by Molecular Beam Epitaxy. Journal of Electronic Materials, 2014, 43, 931-937.	2.2	11
9	Current–Voltage Characteristics of GeSn/Ge Heterojunction Diodes Grown by Molecular Beam Epitaxy. IEEE Electron Device Letters, 2013, 34, 1217-1219.	3.9	15
10	Photoconductivity of germanium tin alloys grown by molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	3.3	34
11	Infrared electroluminescence from GeSn heterojunction diodes grown by molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	3.3	86
12	Lattice constant and substitutional composition of GeSn alloys grown by molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	87
13	The properties of germanium-tin alloys for infrared device applications. , 2011, , .		1
14	Magnetic tunneling junction based magnetic field sensors: Role of shape anisotropy versus free layer thickness. Journal of Applied Physics, 2011, 109, .	2.5	11